NTT AT

NTT-AT provides GaN epitaxial wafers with hign mobility for electronic devices

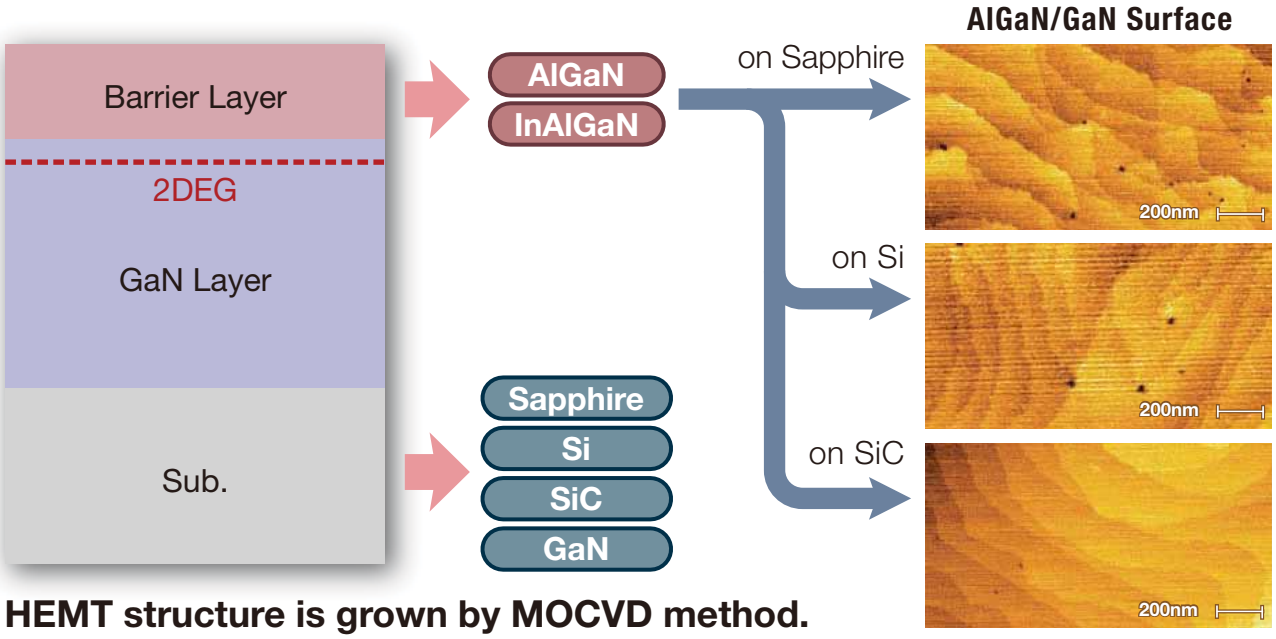
GaN EPITAXIAL WAFERS

- GaN epitaxial wafers using various substrates (Sapphire, Si, SiC, GaN)
- Able to provide large size substrate (up-to 6 inch with Si substrate)
- Widely accepted by the electronic device market
- Novel fabrication technique based on the cutting-edge techniques of NTT Laboratories

GaN HEMT Epi Products

Epi	Size	Substrate
AlGaN/GaN HEMT Epi	2～6 inch	Sapphire
	2～6 inch	Si
	2～4 inch	SiC
	2 inch	GaN

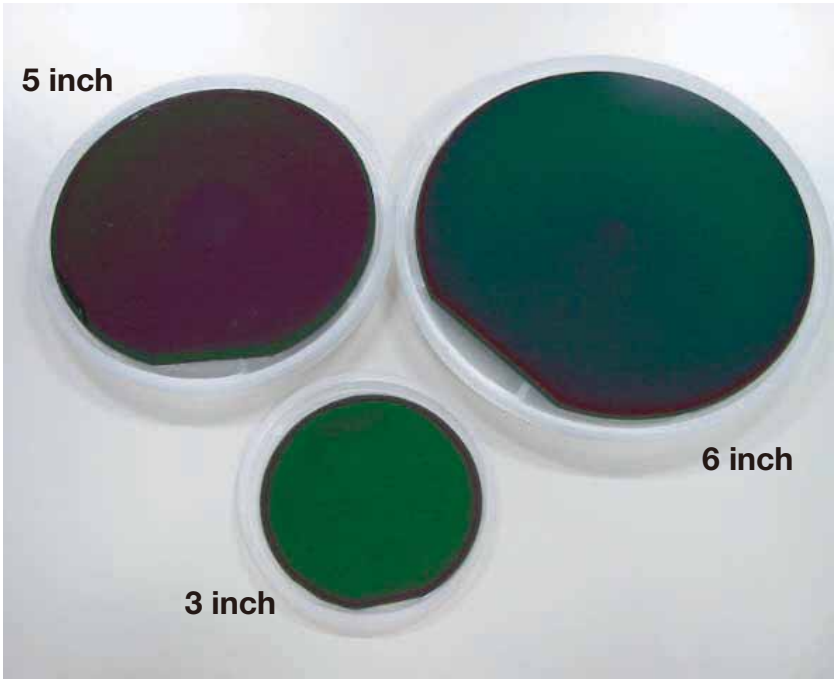
Layer Structure and AFM Images of HEMT epi surface



HEMT structure is grown by MOCVD method.

We are successed in growing an AlGaN/GaN HEMT structure on Si sub.

GaN Epitaxial Wafers



Standard fabrication process

1. Formulate crystal growth conditions
2. Substrate cleaning
3. Expitaxial growth
4. Non destructive inspection of crystal quality by X-ray diffraction

Other optional inspection services are available to meet your needs

- Thickness uniformity
- Composition uniformity
- Sheet resistance
- Mobility
- AFM
- Surface particle inspection

► NTT-AT is pleased to “customize” our GaN epi-wafer according to your needs.

► Please let us know your required layer structure and quantity.
For any further questions, please feel free to contact us.

Notes:
This content may be subject to change without notice.
This product has been classified under Item 7(18) in the Export Control Order Attachment List 1 by Japan's Ministry of Economy, Trade and Industry (METI), and a license from METI is required for its export.

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